MIL-S-19500/208B LL August 1967 SUPERSEDING MIL-S-19500/208A (EL) 23 October 1964 (See 6.2)

#### MILITARY SPECIFICATION

# SEMICONDUCTOR DEVICE, TRANSISTOR, NPN, SILICON, HIGH-POWER TYPES 2N1487, 2N1488, 2N1489, AND 2N1490

This specification is mandatory for use by all Departments and Agencies of the Department of Defense.

#### 1. SCOPE

- 1.1 Scope. This specification covers the detail requirements for a silicon, NPN, high-power transistor.
  - 1.2 Physical dimensions. See figure 1 (TO-3).

#### 1.3 Maximum ratings.

P <sub>C</sub> <u>1</u> /		во	$v_{EBO}$	v <sub>C</sub>	EO	v <sub>C</sub>	EX	I <sub>C</sub>	IB	Tstg	θJ-C	$T_{\mathbf{J}}$
$T_C = 25^{\circ}C$	2N1487 2N1489	2N1488 2N1490		2N1487 2N1489	2N1488 2N1490	2N1487 2N1489	2N1488 2N1490					
w	<u>Vdc</u>	<u>Vdc</u>	<u>Vdc</u>	Vdc	<u>Vdc</u>	<u>Vdc</u>	<u>Vdc</u>	Adc	Adc	°C	°C/W	၁
75	60	100	10	40	55	60	100	6	3	-65 to +200	2. 33	+ 200

<sup>1/</sup> Derate linearly 0.429 W/°C for T<sub>C</sub>>25°C.

# 1.4 Primary electrical characteristics.

	h <sub>FE</sub> -V <sub>CE</sub> = 4 I <sub>C</sub> = 1 2N1487 2N1488	1. 0 Vdc 1. 5 Adc 2N1489	I <sub>C</sub> = 1 I <sub>B</sub> = 300 mAdc 2N1487	2N1489	$V_{CE} = 4$ $I_{C} = 1$ $2N1487$	3E 1/4.0 Vdc 1.5 Adc 2N1489 2N1490	V <sub>CB</sub> = 30 Vdc	<sup>I</sup> EBO V <sub>EB</sub> = 10 Vdc	$f_{ m hfb}$ V $_{ m CE}$ = 12 Vdc $_{ m I}_{ m C}$ = 100 mAdc
			<u>Vdc</u>	Vdc	Vdc	<u>Vdc</u>	<u>μ</u> Adc	μAdc	<u>kc</u>
Min Max	15 45	25 75	3. 0	1. 0	3. 0	2.0	25	25	500 

<sup>1/</sup> Pulsed (see 4.4.1).

# 2. APPLICABLE DOCUMENTS

2.1 The following documents, of the issue in effect on date of invitation for bids or request for proposal, form a part of the specification to the extent specified herein.

# **SPECIFICATION**

## **MILITARY**

MIL-S-19500 - Semiconductor Devices, General Specification for.

#### **STANDARDS**

#### **MILITARY**

MIL-STD-202 - Test Methods for Electronic and Electrical Component Parts. MIL-STD-750 - Test Methods for Semiconductor Devices,

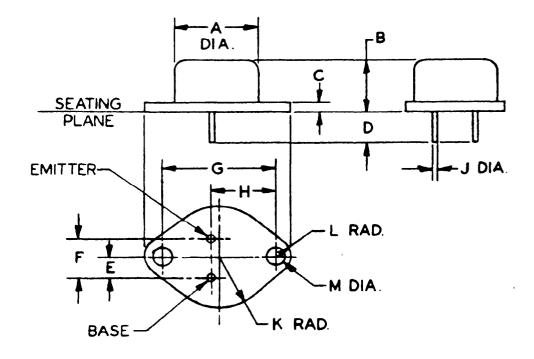
(Copies of specifications, standards, drawings, and publications required by suppliers in connection with specific procurement functions should be obtained from the procuring activity or as directed by the contracting officer.)

## 3. REQUIREMENTS

- 3.1 General. Requirements shall be in accordance with MIL-S-19500, and as specified herein.
- 3.2 Abbreviations, symbols, and definitions. The abbreviations, symbols, and definitions used herein are defined in MIL-S-19500.
- 3.3 Design, construction, and physical dimensions. The transistors shall be of the design, construction, and physical dimensions shown on figure 1.
- 3.4 Performance characteristics. Performance characteristics shall be as specified in tables I, II, and III.
- 3.5 Marking. The following marking specified in MIL-S-19500 may be omitted from the body of the transistor at the option of the manufacturer:
  - (a) Country of origin.
  - (b) Manufacturer's identification.

#### 4. QUALITY ASSURANCE PROVISIONS

- 4.1 Sampling and inspection. Sampling and inspection shall be in accordance with MIL-S-19500, and as specified herein.
- 4.2 Qualification inspection. Qualification inspection shall consist of the examinations and tests specified in tables I, II, and III.
- 4.3 Quality conformance inspection. Quality conformance inspection shall consist of groups A, B, and C inspections.
- 4.3.1 Group A inspection. Group A inspection shall consist of the examinations and tests specified in table I.
- 4.3.2 Group B inspection. Group B inspection shall consist of the examinations and tests specified in table II.
- 4.3.3 Group C inspection. Group C inspection shall consist of the examinations and tests specified in table III. This inspection shall be conducted on the initial lot and thereafter every 6 months during production.
- 4.3.4 Group B and group C life-test samples. Samples that have been subjected to group B, 340-hours life-test, may be continued on test to 1000-hours in order to satisfy group C life-test requirements. These samples shall be predesignated, and shall remain subjected to the group C 1,000-hour acceptance evaluation after they have passed the group B, 340-hour acceptance criteria. The cumulative total of failures found during 340-hour test and during the subsequent interval up to 1,000 hours shall be computed for 1,000-hour acceptance criteria.



# NOTES:

- 1. Metric equivalents (to the nearest .01 mm) are given for general information only and are based upon 1 inch = 25.4 mm.
- 2. This dimension should be measured at points .050 (1.27 mm) to .055 (1.40 mm) below seating plane. When gage is not used, measurement will be made at seating plane.
- 3. Two leads.
- 4. Collector shall be electrically connected to the case.

DIMENSIONS								
LTR	INC	HES	MILLIM	Z OH-wળ				
LIK	MIN MAX		MIN	MAX	Š			
A		.875		22.23				
В	<b>.</b> 250	.450	6.35	11.43				
С		.135		3.43				
D	.312		7.92		3			
E	.205	.225	5.21	5.72				
F	.420	.440	10.67	11.18				
G	1.177	1.197	29.90	30.40				
·H	.665	.675	16.64	17.15	'2			
J	.038	.043	.97	1.09	3			
K		.525		13.34				
L		.188		4.78				
M	.151	.161	3.84	4.09				

FIGURE 1. Physical dimensions of transistor types 2N1487, 2N1488, 2N1489 and 2N1490 (TO-3).

- $4.4\,$  Methods of examination and test. Methods of examination and test shall be as specified in tables I, II, and III.
- 4. 4. 1 Pulse measurements. Conditions for pulse measurement shall be as specified in section 4 of MIL-STD-750.
- 4. 4. 2 Interval for end-point test measurements. End-point tests shall be completed within the following time limitations, after completion of the last test in the subgroup:
  - (a) Qualification inspection: within 24 hours.
  - (b) Quality conformance inspection: within 96 hours.

TABLE I. Group A inspection

Examination or test		MIL-STD-750			Limits		5
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 1			10				
Visual and mechanical examination	2071						
Subgroup 2			5				
Breakdown voltage, collector to emitter	3011	Bias cond. D; I <sub>C</sub> = 100 mAdc; pulsed (see 4.4.1)		BVCEO			
2N1487, 2N1489					40		Vdc
2N1488, 2N1490					55		Vdc
Breakdown voltage, collector to base	3001	Bias cond. D; $I_C = 200 \mu Adc$		<sup>BV</sup> CBO			
2N1487, 2N1489					60		Vdc
2N1488, 2N1490					100		Vdc
Breakdown voltage, collector to emitter	3011	Bias cond. A; V <sub>EB</sub> = 1.5 Vdc;   I <sub>C</sub> = 0.5 mAdc		BVCEX			
2N1487, 2N1489					60		Vdc
2N1488, 2N1490					100		Vdc
Collector to base cutoff current	3036	Bias cond. D; V <sub>CB</sub> = 30 Vdc		I <sub>CBO</sub>		<b>2</b> 5	μ <b>A</b> dc
Emitter to base cutoff current	3061	Bias cond. D; V <sub>EB</sub> = 10 Vdc		I <sub>EBO</sub>		<b>2</b> 5	μ <b>A</b> dc
Subgroup 3			5		1		
Forward-current transfer ratio	3076	V <sub>CE</sub> = 4.0 Vdc: I <sub>C</sub> = 1.5 Adc; pulsed (see 4.4.1)		hFE			
2N1487, 2N1488	;			į	15	45	
2N1489, 2N1490	j				<b>2</b> 5	75	

TABLE I. Group A inspection - Continued

		MIL-STD-750					
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 3 - Continued							
Collector to emitter voltage (saturated)	3071			V <sub>CE</sub> (sat)			
2N1487, 2N1488		I <sub>C</sub> = 1.5 Adc: I <sub>B</sub> = 300 mAdc; pulsed (see 4.4.1)				3.0	Vdc
2N1489, 2N1490		I <sub>C</sub> = 1.5 Adc; I <sub>B</sub> = 100 mAdc; pulsed (see 4.4.1)			= = =	1.0	Vdc
Base emitter voltage (nonsaturated)	3066	Test cond. B, V <sub>CE</sub> = 4.0 Vdc; I <sub>C</sub> = 1.5 Adc; pulsed (see 4.4.1)		v <sub>BE</sub>			
2N1487, 2N1488		pursed (see 4.4.1)				3.0	Vdc
2N1489, 2N1490		:				2.0	Vdc
Subgroup 4			10				
Small-signal short-circuit forward-current transfer- ratio cutoff frequency	3301	V <sub>CB</sub> = 12 Vdc; I <sub>C</sub> = 100 mAdc		fhfb	500		kc
Open-circuit output capacitance	3236	$V_{CB} = 10 \text{ Vdc}; I_{E} = 0;$ $100 \text{ kHz} \le f \le 1 \text{ MHz}$	;	C <sub>obo</sub>		700	pf
Pulse response	3251	Test cond. A; $V_{CC} = 12 \text{ Vdc}$ ; $I_{B}^{(0)} = I_{B}^{(2)} = 150 \text{ mAdc}$ ; $I_{B}^{(1)} = 300 \text{ mAdc}$ ; $R_{C} = 7.8 \text{ ohms}$		t <sub>on</sub> + t <sub>of</sub>		25	μsec
Subgroup 5	,	:	15				
High-temperature operation:	:	$T_A = +175^{\circ}C$					:
Collector to base cutoff current	3036	Bias cond. D; V <sub>CB</sub> = 30 Vdc		<sup>I</sup> CBO		1. 0	mAdo
Low-temperature operation:		<b>T</b> <sub>A</sub> = -55°C			1	,	İ
Forward-current transfer ratio	3076	V <sub>CE</sub> = 4.0 Vdc; I <sub>C</sub> = 1.5 Adc pulsed (see 4.4.1)	; <sup>!</sup>	h <sub>FE</sub>			
2N1487, 2N1488	1				10		
2N1489, 2N1490					15		
		•	i i	İ			
	i			1	1		
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					i	:	
					;	1	

TABLE II. Group B inspection

Examination or test		MIL-STD-750	LTPD			Limit	5	
	Method	Details	LIPD	Symbol	Min	Max	Unit	
Subgroup 1			20					
Physical dimensions	2066	(See figure 1)						
Subgroup 2			15					
Solderability	2026	Omit aging; dwell time = 10 ±1 sec						
Thermal shock (temperature cycling)	1051	Test cond. C						
Thermal shock (glass strain)	1056	Test cond. B						
Terminal strength (tension)	2036	Test cond. A; weight = 10 lbs; time = 15 sec						
Terminal strength (lead torque)	2036	Test cond. D1; torque = 6 in-oz; time = 15 sec						
Seal (leak-rate)		MIL-STD-202, method 112, test cond. C, procedure III; test cond. A for gross leaks				5x10 <sup>-7</sup>	atm cc/sed	
Moisture resistance	1021	Omit initial conditioning						
End points: (See 4.4.2.)								
Collector to base cutoff current	3036	Bias cond. D; V <sub>CB</sub> = 30 Vdc		<sup>I</sup> СВО		25	μ <b>Adc</b>	
Forward-current transfer ratio	3076	V <sub>CE</sub> = 4.0 Vdc; I <sub>C</sub> = 1.5 Adc		h <sub>FE</sub>				
2N1487, 2N1488					15	45		
2N1489, 2N1490					<b>2</b> 5	75		
Subgroup 3	j		10	į			İ	
Shock	2016	Nonoperating; 500 G, 1.0 msec, 5 blows in each orientation: $X_1$ , $Y_1$ , $Y_2$ , and $Z_1$						
Vibration fatigue	2046	Nonoperating						
Vibration, variable frequency	2056							
Constant acceleration	4	5000 G in each orientation: $X_1$ , $Y_1$ , $Y_2$ , and $Z_1$						
End points:	1							
(Same as for subgroup 2)							1	
	:							

TABLE II. Group B inspection - Continued

		MIL-STD-750	I mnn		Limits		
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 4			20				
Salt atmosphere (corrosion)	1041						
End points:							
(Same as for subgroup 2)							
Subgroup 5			10	5 			
Burnout by pulsing	3005	Prepulse cond.: T <sub>A</sub> = 25°C; V <sub>CE</sub> = 0; I <sub>C</sub> = 0					
		Pulse cond.: T <sub>A</sub> = 25°C; t <sub>p</sub> = 1 sec; test cycles = 1					
Test #1		V <sub>CE</sub> = 12.5 Vdc;					
(All types)		I <sub>C</sub> = 6.0 Adc					
Test #2		V <sub>CE</sub> = 40 Vdc;	1				
2N1487, 2N1489		I <sub>C</sub> = 1.875 Adc					
Test #3		V <sub>CE</sub> = 55 Vdc;				İ	
2N1488, 2N1490		I <sub>C</sub> = 1.36 Adc					
End points:							
(Same as for subgroup 2)							
Subgroup 6			10				
Clamped-inductive sweep test		(See figure 2)	; ;	===	= <del>=</del> =		:   
Unclamped-inductive sweep test		(See figure 3 and 4)					
End points:		!   			!		 
(Same as for subgroup 2)							1
Subgroup 7			7			1	•
High-temperature life (nonoperating)	1031	T <sub>stg</sub> = +200° C; time = 340 hours (see 4.3.4)					
End points: (See 4.4.2.)				:			
Collector to base cutoff current	3036	Bias cond. D; V <sub>CB</sub> = 30 Vdc		ICBO		50	μ <b>A</b> dc
Forward-current transfer ratio	3076	V <sub>CE</sub> = 4.0 Vdc; I <sub>C</sub> = 1.5 Adc		h <sub>FE</sub>			
2N1487, 2N1488		!			10	70	
2N1489, 2N1490					18	115	

TABLE II. Group B inspection - Continued

		MIL-STD-750			Limits		
Examination or test	Method	Details	LTPD	Symbol	Min	Max	Unit
Subgroup 8			10				
Steady-state operation life	1026	100° C $\leq$ T <sub>C</sub> $\leq$ 125° C; V <sub>CE</sub> = 24 Vdc; P <sub>C</sub> = 32 W + 125° C - T <sub>C</sub> 2.33° C/W time = 340 hours (see 4.3.4)					
End points: (Same as for subgroup 7)		, , ,					

# TABLE III. Group C inspection

		BLE III. Group C hispection					
		MIL-STD-750	LTPD		]	Limits	
Examination or test	Method	Details	LIPD	Symbol	Min	Max	Unit
Subgroup 1			20				
Barometric pressure, reduced (altitude operation)	1001	Pressure = 8 mm Hg, normal mounting; time = 1 minute					
Measurement during above test:							
Collector to base cutoff current	3036	Bias cond. D		СВО			
2N1487, 2N1489		$v_{CB} = 60 \text{ Vdc}$				200	μAdc
2N1488, 2N1490		V <sub>CB</sub> = 100 Vdc				200	μ <b>A</b> dc
Thermal resistance (junction to case)	3151			<sup>θ</sup> J-C		2. 33	°C/W
Subgroup 2			λ=10				
High-temperature life (nonoperating)	1031	T <sub>sty</sub> = +200° C (see 4.3.4)					
End points: (See 4, 4, 2, )							1
Collector to base cutoff current	3036	Bias cond. D; V <sub>CB</sub> = 30 Vdc		Ісво		50	μ <b>A</b> dc
Forward-current transfer ratio	3076	$V_{CE} = 4.0 \text{ Vdc}; I_{C} = 1.5 \text{ Adc}$		h <sub>FE</sub>			
2N1487, 2N1488					10	70	
2N1489, 2N1490					18	115	
Subgroup 3			λ = 10				
Steady-state operation life	1026	$ \begin{array}{ll} 100^{\circ} \text{ C} \leq \text{T}_{\text{C}} \leq & 125^{\circ}\text{C}; \\ \text{V}_{\text{CE}} = & 24 \text{ Vdc}; \\ \text{P}_{\text{C}} = & 32 \text{ W} + \frac{125^{\circ} \text{ C} - \text{T}_{\text{C}}}{2.33^{\circ} \text{ C/W}} \\ \text{(see 4.3.4)} \end{array} $					
End points:		(SCC 1.0.1)					
(Same as for subgroup 2)							

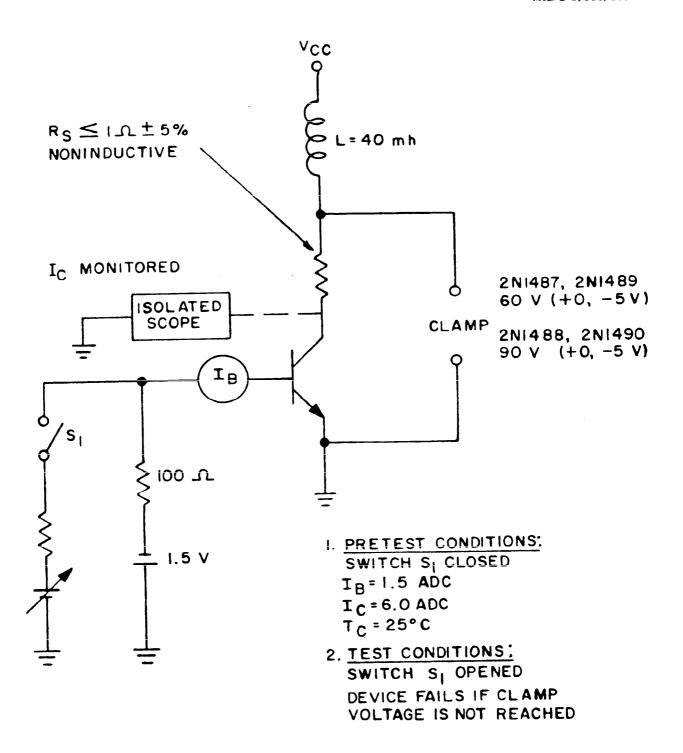


FIGURE 2. Clamped-inductive sweep test circuit.

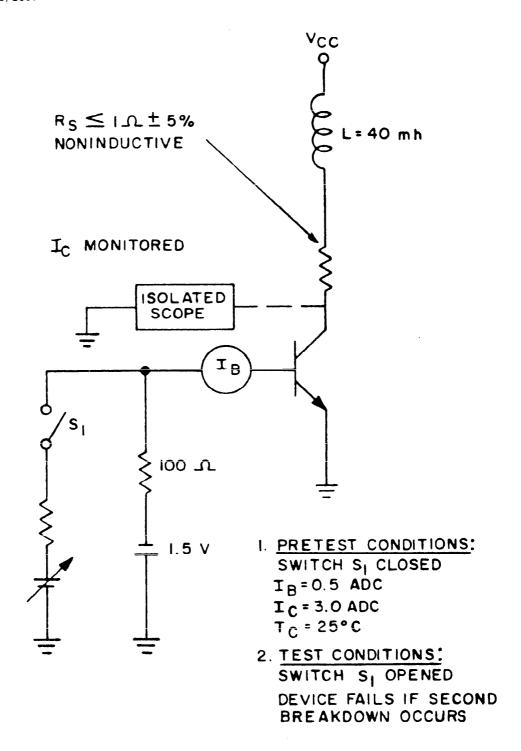


FIGURE 3. Unclamped-inductive sweep test circuit.

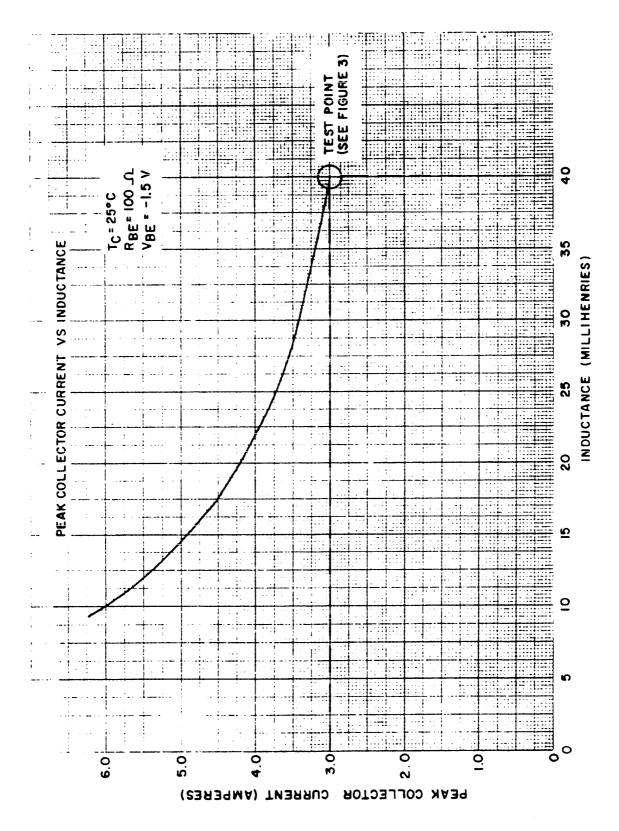


FIGURE 4. Unclamped inductive sweep test curve.

#### MIL-S-19500/208B

- 5. PREPARATION FOR DELIVERY
- 5.1 See MIL-S-19500, section 5.
- 6. NOTES
- 6.1 Notes. The notes specified in MIL-S-19500 are applicable to this specification.
- 6.2 Types covered by superseded specification. Transistor types 2N1511 through 2N1514 have been deleted from this specification. These types (TO-36 case) are no longer manufactured. Transistor types 2N1487 through 2N1490, respectively, are electrically interchangeable with the deleted types and, with suitable mounting modifications, may be used as replacement items. Types having the "USA" prefix are interchangeable with those of corresponding type designation.
- 6.2.1 <u>Disposition of deleted types.</u> Types 2N1511 through 2N1514, as specified in the superseded specification, may be issued until present stock is depleted.
- 6.3 Changes from previous issue. Asterisks are not used in this revision to identify changes with respect to the previous issue, due to the extensiveness of the changes.

Custodians:

Army - EL Navy - SH

Air Force - 11

Review activities:

Army - EL, MU, MI Navy - SH

Air Force - 11, 17, 85

User activities:

Army - EL, SM Navy - CG, MC, AS, OS

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